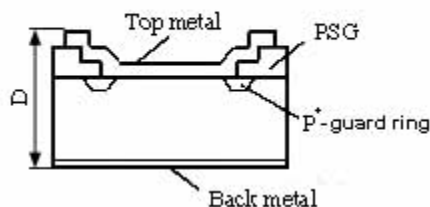
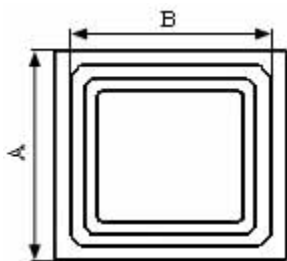




4A/60V. Die Size-65mil.

Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10\text{mA}$	$V_{BR}$	V	60	65
Average Rectified Forward Current	$I_{F(AV)}$	A	4,0	-
DC Forward Voltage @ 25°C, $I_F=4,0\text{A}$	$V_F$	V	0,74	0,72
Maximum Reverse Current @ 25°C, $V_R=60\text{V}$ @ 125°C, $V_R=60\text{V}$	$I_R$	mA	0,010 10,0	0,008 8,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	110	-
Peak Repetitive Reverse Surge Current @ 2,0µs, f=1kHz., $T_J<175^\circ\text{C}$ .	$I_{RRM}$	A	2,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	$V_{ESD}$	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	$T_J$	°C	175	



DIM	ITEM	µm
$A_x$ $A_y$	Wafer Form Die Size	1650 1650
$B_x$ $B_y$	Top Metal Size	1510 1510
D	Thickness	300max.
Scribe line Width		80

Top metal:

a) **Al-Ni-Ag** – for Soldering;

b) **Al** – for Wire Bonding.

Backside metal: **Ti-Ni-Ag**.